

## ABSTRACT

A semiconductor device comprising a first semiconductor region and a second semiconductor region,

- (a) wherein a field effect transistor is comprised of the first  
5 semiconductor region comprising at least one semiconductor layer(s)  
protruding upward from a substrate, a gate electrode(s) formed via an  
insulating film such that the gate electrode(s) strides over the semiconductor  
layer(s) and source/drain regions provided in the semiconductor layer(s) on  
both sides of the gate electrode(s), whereby a channel region is formed in at  
10 least both sides of the semiconductor layer(s),
- (b) wherein the second semiconductor region comprises semiconductor  
layers protruding upward from the substrate and placed, at least opposing the  
first semiconductor region at both ends in the direction perpendicular to a  
channel current direction and the side surface of the semiconductor layers  
15 facing the first semiconductor region is parallel to the channel current direction.